

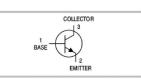


Features:

- Epitaxial planar die construction.
- Complementary PNP type available (MMBT3906).
- Collector Current Capability I_c = 200mA.
- Collector-emitter Voltage $V_{CEO} = 40V$.

Applications:

General switching and amplification.





SOT-23

Maximum Rating: @ TA = 25°C unless otherwise specified

Parameter	Symbol	Conditions	Min.	Max.	Unit
Collector-Base Voltage	V _{CBO}	Open Emitter	60	-	
Collector-Emitter Voltage	V _{CEO}	Open Base	40	-	V
Emitter-Base Voltage	V _{EBO}	Open Collector	6	-	
Collector Current (DC)	I _c		-	200	
Peak Collector Current	I _{CM}		-	200	mA
Peak Base Current	I _{BM}		-	100	
Total Power Dissipation	P _{tot}	Tamb ≤ 25°C	-	250	mW
Storage Temperature	T _{stg}		-65	+150	
Junction Temperature	T _j		-	150	°C
Operating Ambient Temperature	T _{amb}		-65	+150	

Electrical Characteristics: @ TA = 25°C unless otherwise specified

Parameter	Symbol	Conditions	Min.	Max.	Unit
Collector Cut-off Current	I _{CBO}	I _E = 0; V _{CB} = 30V	-	50	
Emitter Cut-off Current	I _{EBO}	I _C = 0; V _{EB} = 6V	-	50	nA
DC Current Gain	h _{FE}	$V_{CE} = 1 V;$ $I_{C} = 0.1 \text{mA}$ $I_{C} = 1 \text{mA}$ $I_{C} = 10 \text{mA}$ $I_{C} = 50 \text{mA}$ $I_{C} = 100 \text{mA}$	60 80 100 60 30	- 300 -	

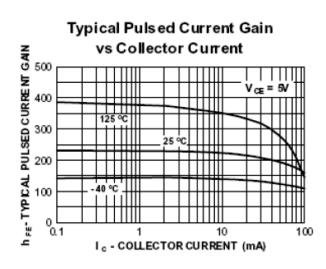


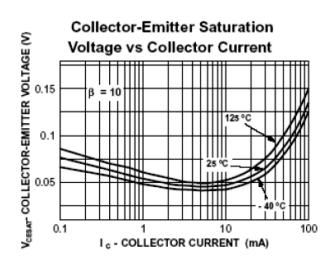


Parameter	Symbol	Conditions	Min.	Max.	Unit	
Colletor-Emitter Saturation Voltage	V _{CE (sat)}	I _C = 10mA; I _B = 1mA	-	200		
		I _C = 50mA; I _B = 5mA	-	300	mV	
Base-emitter Saturation Voltage	V _{BE (sat)}	$I_C = 10\text{mA}; I_B = 1\text{mA}$	650	850] '''	
		$I_{\rm C}$ = 50mA; $I_{\rm B}$ = 5mA	-	950		
Collector Capacitance	C _c	$I_{E} = I_{e} = 0; V_{CB} = 5V;$ f = 1MHz	-	4	25	
Emitter Capacitance	C _e	$I_{c} = I_{c} = 0; V_{BE} = 500 \text{mV};$ f = 1MHz	-	8	− pF	
Transition Frequency	f _T	I _C = 10mA; V _{CE} = 20V; f = 100MHz	300	-	MHz	
Noise Figure	F	$I_{c} = 100 \text{mA}; V_{cE} = 5 \text{V};$ $R_{s} = 1 \text{k}\Omega; f = 10 \text{Hz} \text{ to} 15.7 \text{kHz}$	-	5	dB	
Switching times (between 10% and 9	0% levels);		•			
Delay Time	t _d		-	25		
Rise Time	t _r	I _{Con} = 10mA; I _{Bon} = 1mA;	-	35		
Storage Time	t _s	I _{Boff} = -1mA	-	200	ns	
Fall Time	t _f		-	50		

Note Pulse test: tp≤300 ms; d≤0.02.

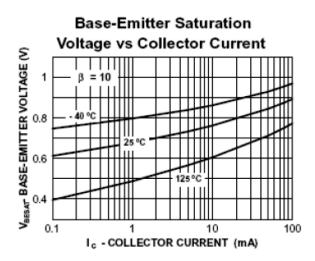
Typical Characteristics: @ TA = 25°C unless otherwise specified

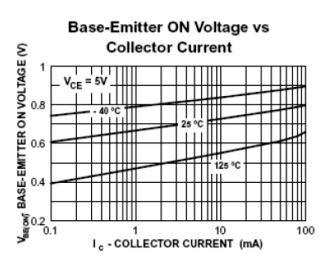


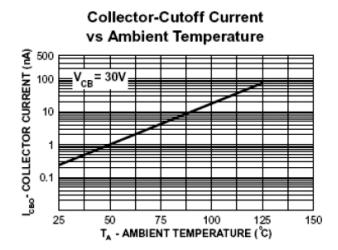


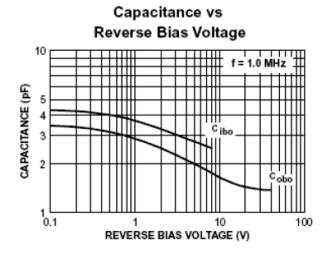






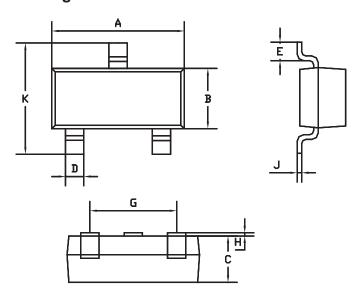






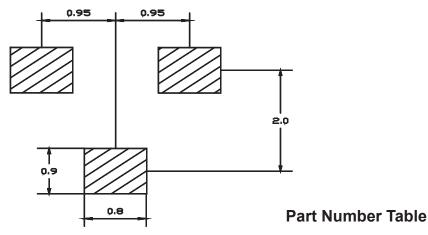


Package Outline:



SOT-23					
Dim	Min.	Max.			
Α	2.85	2.95			
В	1.25 1.35				
С	1 Typical				
D	0.37	0.43			
Е	0.35	0.48			
G	1.85	1.95			
Н	0.02 0.1				
J	0.1 Typical				
K	2.35	2.45			
All Dimensions in mm					

Soldering Footprint:



Dimensions: Millimetres

Description	Part Number	
Transistor, Bipolar, NPN, 40V, 200mA, SOT-23	MMBT3904-7-F	

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